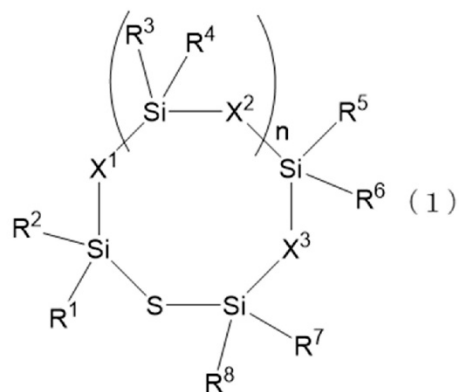


SILICON-CONTAINING FILM PRECURSOR, COMPOSITION FOR
FORMING SILICON-CONTAINING FILM, METHOD FOR MANUFACTURING
SULFUR-CONTAINING SILOXANE, AND METHOD FOR MANUFACTURING
SILICON-CONTAINING FILM

Abstract

Provided is a siloxane compound that can be used as a siloxane-containing film precursor with which it is possible, in the formation of a silicon-containing film, to form a film by atomic layer deposition (ALD) even in high-temperature conditions, by a sulfur-containing siloxane represented by formula (1) (where: R^1 to R^8 are, independently in each occurrence, a hydrogen atom, a C1-5 alkyl group, a C2-5 alkenyl group, a C2-5 alkynyl group, or a C1-5 alkoxy group; R^1 to R^8 may each bond with each other to form a ring; X^1 to X^3 are, independently in each occurrence, an oxygen atom or a sulfur atom; and n is an integer from 0 to 2).



[FIG.2]